**Product data sheet** 

## 1. General description

Silicon Carbide Schottky diode in a TO263 (D2PAK) plastic package, designed for high frequency switched-mode power supplies.



### 2. Features and benefits

- · Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- · Reduced losses in associated MOSFET
- Reduced EMI
- · Reduced cooling requirements
- RoHS compliant

## 3. Applications

- · Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

### 4. Quick reference data

#### Table 1. Quick reference data

| Symbol             | Parameter                       | Conditions                                                                                                            |     | Va  | lues |     | Unit |
|--------------------|---------------------------------|-----------------------------------------------------------------------------------------------------------------------|-----|-----|------|-----|------|
| Absolute           | maximum rating                  |                                                                                                                       |     |     |      |     |      |
| $V_{RRM}$          | repetitive peak reverse voltage |                                                                                                                       |     | 6   | 50   |     | V    |
| I <sub>F(AV)</sub> | average forward current         | $\delta$ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 112 °C;<br>Fig. 1; Fig. 2; Fig. 3                               | 10  |     |      | А   |      |
| T <sub>j</sub>     | junction temperature            |                                                                                                                       | 175 |     |      | °C  |      |
| Symbol             | Parameter                       | Conditions                                                                                                            |     | Min | Тур  | Max | Unit |
| Static ch          | aracteristics                   |                                                                                                                       |     |     |      |     |      |
| V <sub>F</sub>     | forward voltage                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>                                                          |     | -   | 1.5  | 1.7 | V    |
|                    |                                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>                                                         |     | -   | 1.8  | 2.2 | V    |
| Dynamic            | characteristics                 |                                                                                                                       | •   |     |      |     |      |
| Q <sub>r</sub>     | recovered charge                | $I_F = 10 \text{ A}$ ; $dI_F/dt = 500 \text{ A/}\mu\text{s}$ ; $V_R = 400 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7 |     | -   | 14   | -   | nC   |

# 5. Pinning information

**Table 2. Pinning information** 

| Pin | Symbol | Description                         | Simplified outline | Graphic symbol     |
|-----|--------|-------------------------------------|--------------------|--------------------|
| 1   | n.c.   | not connected                       | F-F                | K A                |
| 2   | K      | cathode [1]                         |                    | K — A<br>001aaa020 |
| 3   | А      | anode                               |                    |                    |
| mb  | К      | mounting base; connected to cathode | 1 TO-263 (D2PAK)   |                    |

<sup>[1]</sup> It is not possible to connect to pin 2 of the TO263 package.

# 6. Ordering information

#### **Table 3. Ordering information**

| Type number  | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|--------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| WNSC2D10650B | TO263        | WNSC2D10650BJ         | Reel           | 800                    | TO263N          | 26-Sep-2016        |

# 7. Marking

### Table 4. Marking codes

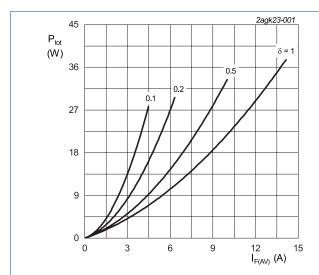
| Type number  | Marking codes    |
|--------------|------------------|
| WNSC2D10650B | WNSC2D<br>10650B |

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                       | Conditions                                                                   | Values     | Unit             |
|--------------------|---------------------------------|------------------------------------------------------------------------------|------------|------------------|
| $V_{RRM}$          | repetitive peak reverse voltage |                                                                              | 650        | V                |
| $V_{RWM}$          | crest working reverse voltage   |                                                                              | 650        | V                |
| $V_R$              | reverse voltage                 | DC                                                                           | 650        | V                |
| I <sub>F(AV)</sub> | average forward current         | $δ$ = 0.5; square-wave pulse; $T_{mb} \le 112$ °C;<br>Fig. 1; Fig. 2; Fig. 3 | 10         | А                |
| I <sub>FRM</sub>   | repetitive peak forward current | $δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 112 °C$ ; square-wave pulse       | 20         | А                |
| I <sub>FSM</sub>   | non-repetitive peak             | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse                        | 50         | Α                |
|                    | forward current                 | $t_p$ = 10 μs; $T_{j(init)}$ = 25 °C; square-wave pulse                      | 450        | А                |
| l <sup>2</sup> t   | I <sup>2</sup> t for fusing     | sine-wave pulse; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 10 ms        | 12.5       | A <sup>2</sup> s |
| T <sub>stg</sub>   | storage temperature             |                                                                              | -55 to 175 | °C               |
| T <sub>j</sub>     | junction temperature            |                                                                              | 175        | °C               |



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$  $V_o = 1.024 \text{ V; R}_s = 0.1156 \Omega$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

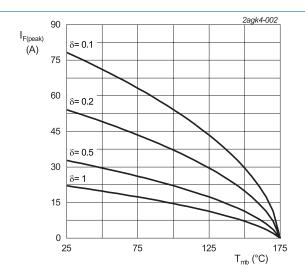
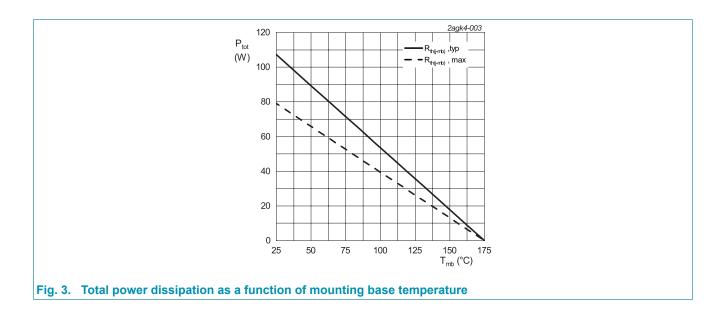


Fig. 2. Current derating as a function of mounting base temperature



## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter                                                  | Conditions  | Min | Тур | Max | Unit |
|-----------------------|------------------------------------------------------------|-------------|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base    | Fig. 4      | -   | -   | 1.8 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient free air | in free air | -   | 50  | -   | K/W  |

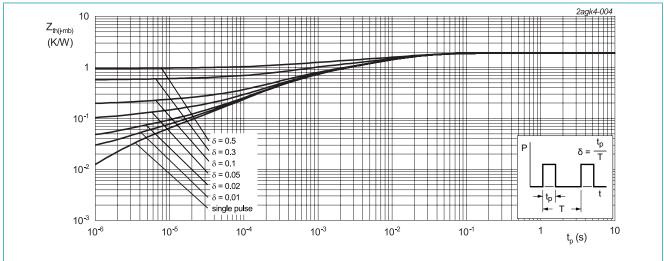
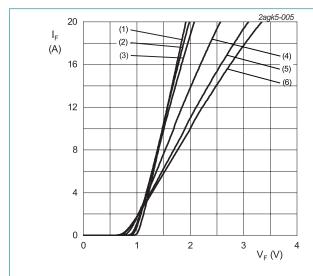


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 10. Characteristics

**Table 7. Characteristics** 

| Symbol          | Parameter                       | Conditions                                                                                                       | Min | Тур | Max | Unit |
|-----------------|---------------------------------|------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| Static cha      | aracteristics                   |                                                                                                                  |     |     |     |      |
| V <sub>F</sub>  | forward current                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>                                                     | -   | 1.5 | 1.7 | V    |
|                 |                                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>                                                    | -   | 1.8 | 2.2 | V    |
|                 |                                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 175 °C; <u>Fig. 5</u>                                                    | -   | 2   | 2.3 | V    |
| I <sub>R</sub>  | reverse current                 | V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>                                                    | -   | 0.5 | 50  | μA   |
|                 |                                 | V <sub>R</sub> = 650 V; T <sub>j</sub> = 175 °C; <u>Fig. 6</u>                                                   | -   | 25  | 250 | μA   |
| Dynamic         | characteristics                 |                                                                                                                  |     |     |     |      |
| Q <sub>r</sub>  | recovered charge                | $I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$ | -   | 14  | -   | nC   |
| C <sub>d</sub>  | diode capacitance               | f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>j</sub> = 25 °C                                                          | -   | 310 | -   | pF   |
|                 |                                 | f = 1 MHz; V <sub>R</sub> = 300 V; T <sub>j</sub> = 25 °C                                                        | -   | 36  | -   | pF   |
|                 |                                 | f = 1 MHz; V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C                                                        | -   | 32  | -   | pF   |
| E <sub>as</sub> | non-repetitive avalanche energy | I <sub>R</sub> = 5.5 A; L = 5 mH; T <sub>j(init)</sub> = 25 °C                                                   | 75  | -   | -   | mJ   |



 $V_o$  = 1.024 V;  $R_s$  = 0.1156  $\Omega$ 

(1)  $T_j$  = -55 °C; typical values

(2) T<sub>j</sub> = 0 °C; typical values

(3) T<sub>i</sub> = 25 °C; typical values

(4)  $T_i = 100 \,^{\circ}\text{C}$ ; typical values

(5) T<sub>j</sub> = 150 °C; typical values (6) T<sub>j</sub> = 175 °C; typical values

Fig. 5. Forward current as a function of forward

voltage; typical values

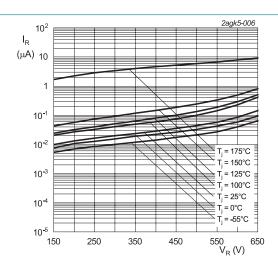
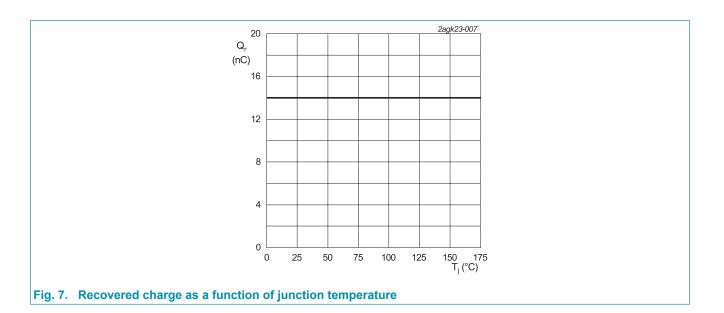
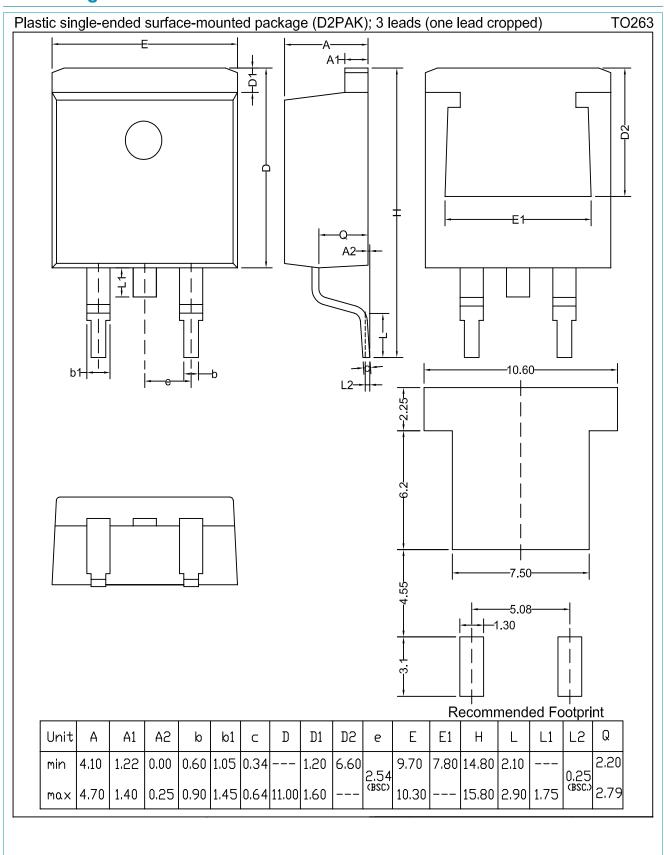


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value



## 11. Package outline



## 12. Legal information

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| Document status [1][2]               | Product status [3] | Definition                                                                            |
|--------------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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